

Kunal Kumar (羅庫納)



- **Contact Information**

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(Please contact with me mostly by email many times, i have no mobile with me)
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- ◆ Linkedin: <https://www.linkedin.com/in/kunal-kumar-he-him-his-729b3ba6/>

- ◆ **Working Experiences**

- 1. Flexium Interconnect Inc.**

Kaohsiung Taiwan 03/2023 (Continues)

Project Engineer -RF (Analog Design), Circuit Design using Cadence Allegro / OrCAD, Signal and Power Integrity Simulation, Knowledge of probe station, measurements of RF and Semiconductor Devices, Network Analyzers, Oscilloscope, ADS (Keysight), soldering iron , Sentaurus TCAD .

- 2. FENIX Process Technologies Pvt. Ltd,**

Pune India 09/2015~02/2017

Graduate Test Engineer, Electronic components Hardware Test Engineer, PCB Circuit Design using OrCAD, measurements of signal Using Analyzer.

- 3. VNC Group**

Chennai India 06/1012~12/2014

Product Engineer, measurements of passive components electrical characteristics

- **Interested Job Positions**

- ◆ *TCAD Engineer.*
- ◆ *Semiconductor Device Design or Process Engineer.*
- ◆ *PCB Circuit Design Engineer or Simulation Engineer.*

- **Education**

- ◆ *Doctor of Philosophy in Electrical Engineering* Apr. 2017 – Dec 2022
National Cheng Kung University (NCKU), Tainan, Taiwan.
Advisor: Prof. Yeong Her Wang (Pres of NAR LAB Taiwan Gov.)
- ◆ *Master of Technology in Electrical Engineering* June. 2014 – July2016
Indian Institute of Technology, Patna, India
- ◆ *Bachelor of Technology in Electronics and communication*

- **Publications**

- **Journal papers**

- ◆ **Kunal Kumar** at all “Significance of multivalley and nonparabolic band structure for GeSn TFET simulation “ IEEE Transactions on Electron Devices..., 2018.
- ◆ **Kunal Kumar** at all “MOS structure CV analysis under process integration and simulation “Under review in IEEE TED.
- ◆ **Kunal Kumar.** “Comparative Study of Symmetric and Asymmetric Oxide Double Gate Junction less FET” Journal of Semiconductor Devices and Circuits. 2021; 8(2):14–20p.
- ◆ **Kunal kumar** “A simulation based study of Capacitor-less Low-Dropout Regulator (LDO) “Journal of Microelectronics and Solid State Devices. 2021; 8(3): 1–10p.
- ◆ **kunal kumar** “Advanced Work Function Engineering for HighSpeed and Low-Power Ge/Si Hetero Complementary FET Inverters “ under review in IEEE TED.

- **Skills**

- ◆ **TCAD** Based Simulation of semiconductor devices (PhD work) MOSFETs, TFET , FinFETs, POWER MOSFETs.
- ◆ **MATLAB** (characteristics analysis), **COMSOL MULTIPHYSICS** (Device Simulation)
- ◆ **HSPICE** basics (integrated-circuit simulation) , **OrCAD** , **Circuit Lab** ,**LT spice**.

- **Courses during PhD**

- ◆ *Semiconductor Device Modelling & Simulation.*
- ◆ Circuit Simulation and Analysis with HSPICE by NAR Lab.
- ◆ Analog IC Design using Custom Compiler by NAR Lab.
- ◆ *Semiconductor & Advance Nanotechnology Process Introduction (I and II) course taken by TSMC Taiwan.*
- ◆ *Nano-Node Semiconductor Introduction course taken by UMC Taiwan.*

- **Referee**

- ◆ Prof. Yeong Her Wang (886 6 2757575 ext 62352, wangyher@mail.ncku.edu.tw)
- ◆ Prof Sudhan Majhi (+91-612-302 8045 , smajhi@iitp.ac.in)
- ◆ Prof Meng-Hsueh Chiang (+886-6-2757575 ext.62418 , mhchiang@mail.ncku.edu.tw)

- **Declaration**

I Kunal Kumar declare that the above flourished details are true to the best of my knowledge and belief.

Kunal Kumar
Tainan, Taiwan